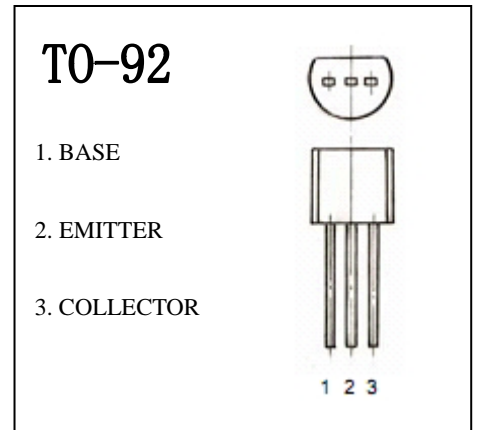


深圳市晶泰源电子有限公司

KSP10 TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	30	V
VCEO	Collector-Emitter Voltage	25	V
VEBO	Emitter-Base Voltage	3	V
IC	Collector Current	0.05	A
PC	Collector Power Dissipation	350	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =100μA, I _B =0	30			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =1mA, I _E =0	25			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _C =100μA, I _C =0	3			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0			0.1	μA
DC current gain	H _{FE}	V _{ce} =10V, I _c =4mA	60		200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =4mA, I _B =0.4mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =4mA, I _B =0.4mA			0.95	V
Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =4mA, f=100MHz	650			MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			0.7	pF

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